2SD2341

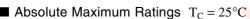
Silicon NPN triple diffusion planar type

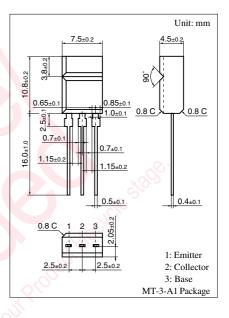
For power amplification

Features

- \bullet Low collector to emitter saturation voltage $V_{CE(sat)}$
- \bullet High collector to emitter voltage V_{CEO}
- Allowing automatic insertion possible with radial taping

Absolute Maximum Ratings $T_c = 25^{\circ}C$					
Parameter	Symbol	Rating	Unit		
Collector to base voltage	V _{CBO}	200	V		
Collector to emitter voltage	V _{CEO}	180	v		
Emitter to base voltage	V _{EBO}	6	V		
Peak collector current	I _{CP}	3	А		
Collector current	I _C	2	А		
Collector power dissipation	P _C	1.5	W		
Junction temperature	Tj	150	°C		
Storage temperature	T _{stg}	-55 to +150	°C		
			. 07		

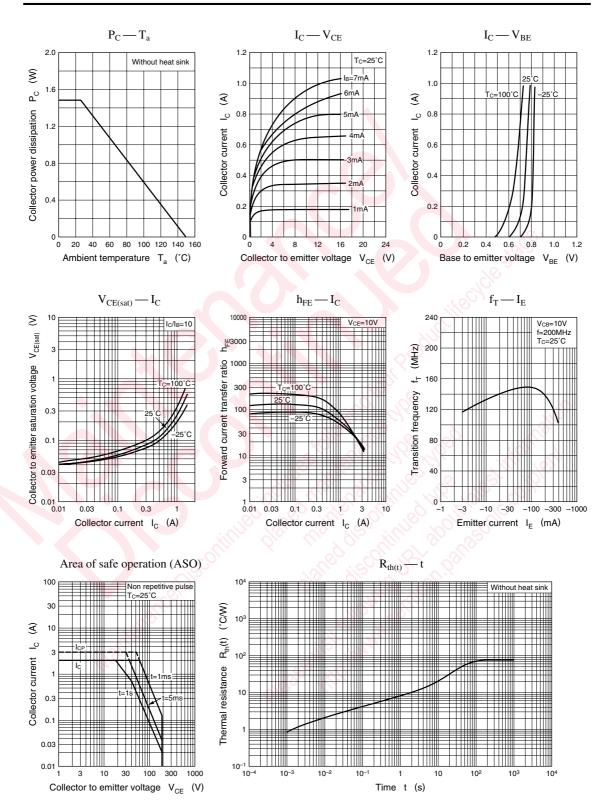




Electrical Characteristics $T_C = 25^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector cutoff current	I _{CBO}	$V_{CB} = 200 \text{ V}, I_E = 0$	15 1	8°	50	μΑ
Emitter cutoff current	I _{EBO}	$V_{EB} = 4 V, I_C = 0$	-02	die	50	μΑ
Collector to base voltage	V _{CBO}	$I_{\rm C} = 500 \ \mu \rm{A}, \ I_{\rm E} = 0$	200	5		V
Collector to emitter voltage	V _{CEO}	$I_{\rm C} = 5 \text{ mA}, I_{\rm B} = 0$	180			V
Emitter to base voltage	℃V _{EBO}	$I_{\rm E} = 500 \mu \rm{A}, I_{\rm C} = 0$	6			V
Forward current transfer ratio	h _{FE1} *	$V_{CE} = 10 \text{ V}, I_C = 150 \text{ mA}$	60		240	
	h _{FE2}	$V_{CE} = 10 \text{ V}, I_{C} = 400 \text{ mA}$	50			
Base to emitter voltage	V _{BE}	$V_{CE} = 10 \text{ V}, I_{C} = 400 \text{ mA}$		1		V
Collector to emitter saturation voltage	V _{CE(sat)}	$I_{\rm C} = 500 \text{ mA}, I_{\rm B} = 50 \text{ mA}$		1		V
Transition frequency	f_{T}	$V_{CB} = 10 \text{ V}, I_{C} = -100 \text{ mA}, f = 200 \text{ MHz}$		150		MHz

Rank	R	S
h _{FE1}	60 to 140	100 to 240



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